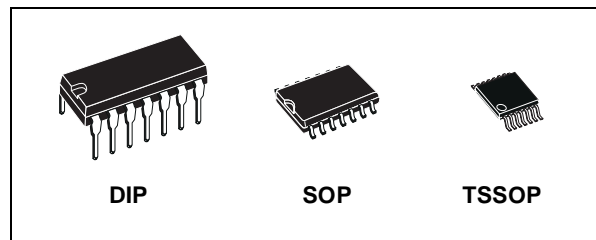




# M74HC77

## 4 BIT D TYPE LATCH

- HIGH SPEED :  
 $t_{PD} = 11 \text{ ns (TYP.) at } V_{CC} = 6V$
- LOW POWER DISSIPATION:  
 $I_{CC} = 2\mu\text{A(MAX.) at } T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 28 \% V_{CC} \text{ (MIN.)}$
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 4\text{mA (MIN)}$
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \cong t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:  
 $V_{CC} \text{ (OPR)} = 2V \text{ to } 6V$
- PIN AND FUNCTION COMPATIBLE WITH  
 74 SERIES 77



### ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HC77B1R	
SOP	M74HC77M1R	M74HC77RM13TR
TSSOP		M74HC77TTR

### DESCRIPTION

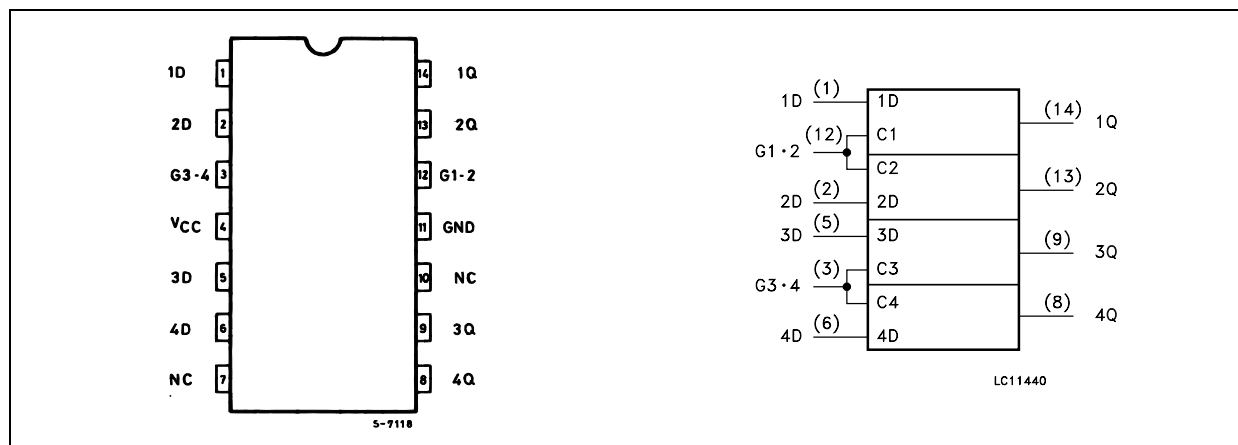
The M74HC77 is an high speed CMOS 4 BIT D TYPE LATCH fabricated with silicon gate C<sup>2</sup>MOS technology.

It contains two groups of 2 bit latches controlled by an enable input (G1•2 or G3•4). These two latch groups can be used in different circuits. The data applied to the data inputs (1D, 2D, or 3D, 4D) are transferred to the Q outputs (1Q, 2Q, or 3Q, 4Q) respectively when the enable input (G1•2 or G3•4)

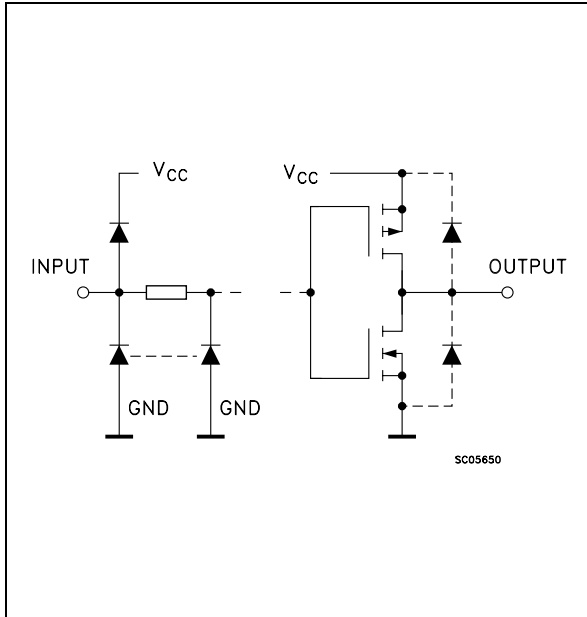
is taken high. The Q outputs will follow the data inputs as long as the enable input is kept high. When the enable input is taken low, the information data applied to the data input is retained at the Q outputs.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

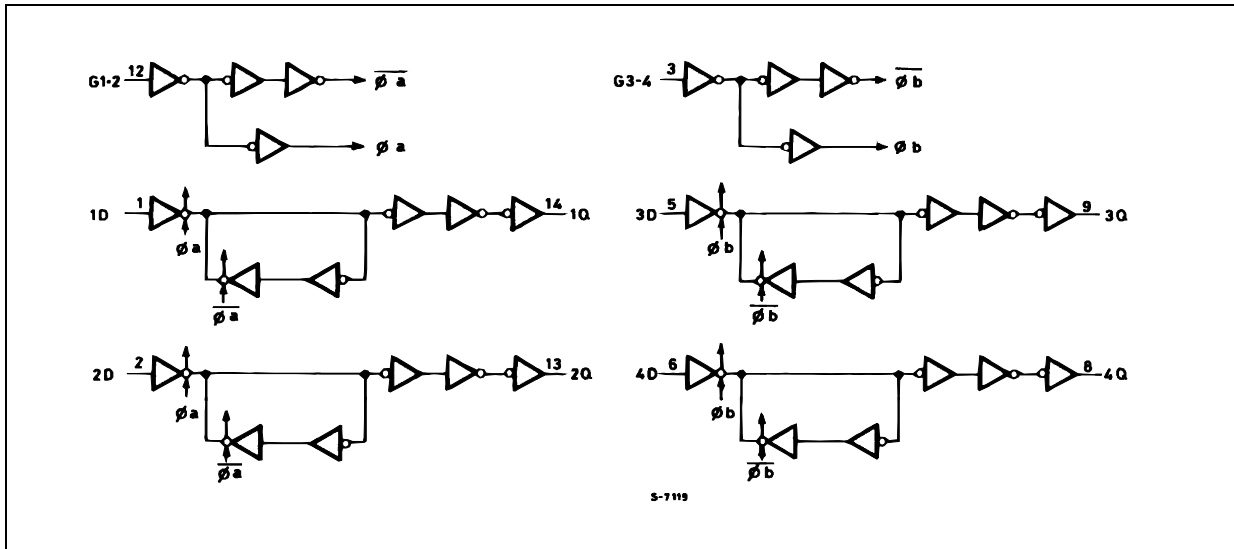
PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 5, 6	1D to 4D	Data Inputs
3	G3 • 4	Latch Enable Input, Latches 3 and 4
7, 10	NC	No Internal Connection
8, 9, 13, 14	1Q to 4Q	Latch Outputs
12	G1 • 2	Latch Enable Input, Latches 1 and 2
11	GND	Ground (0V)
4	V <sub>CC</sub>	Positive Supply Voltage

TRUTH TABLE

INPUTS		OUTPUTS	FUNCTION
D	G	Q	
L	H	L	
H	H	H	
X	L	Qn	LATCH

X : Don't Care

LOGIC DIAGRAM



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	-0.5 to +7	V
$V_I$	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
$V_O$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	DC Input Diode Current	$\pm 20$	mA
$I_{OK}$	DC Output Diode Current	$\pm 20$	mA
$I_O$	DC Output Current	$\pm 25$	mA
$I_{CC}$ or $I_{GND}$	DC $V_{CC}$ or Ground Current	$\pm 50$	mA
$P_D$	Power Dissipation	500(*)	mW
$T_{stg}$	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit	
$V_{CC}$	Supply Voltage	2 to 6	V	
$V_I$	Input Voltage	0 to $V_{CC}$	V	
$V_O$	Output Voltage	0 to $V_{CC}$	V	
$T_{op}$	Operating Temperature	-55 to 125	°C	
$t_r, t_f$	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V <sub>IL</sub>	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V <sub>OH</sub>	High Level Output Voltage	2.0	I <sub>O</sub> =-20 μA	1.9	2.0		1.9		1.9		V
		4.5	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I <sub>O</sub> =-20 μA	5.9	6.0		5.9		5.9		
		4.5	I <sub>O</sub> =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I <sub>O</sub> =-5.2 mA	5.68	5.8		5.63		5.60		
V <sub>OL</sub>	Low Level Output Voltage	2.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		6.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		4.5	I <sub>O</sub> =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I <sub>O</sub> =5.2 mA		0.18	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			± 0.1		± 1		± 1	μA
I <sub>CC</sub>	Quiescent Supply Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			2		20		40	μA

AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6 \text{ ns}$ )

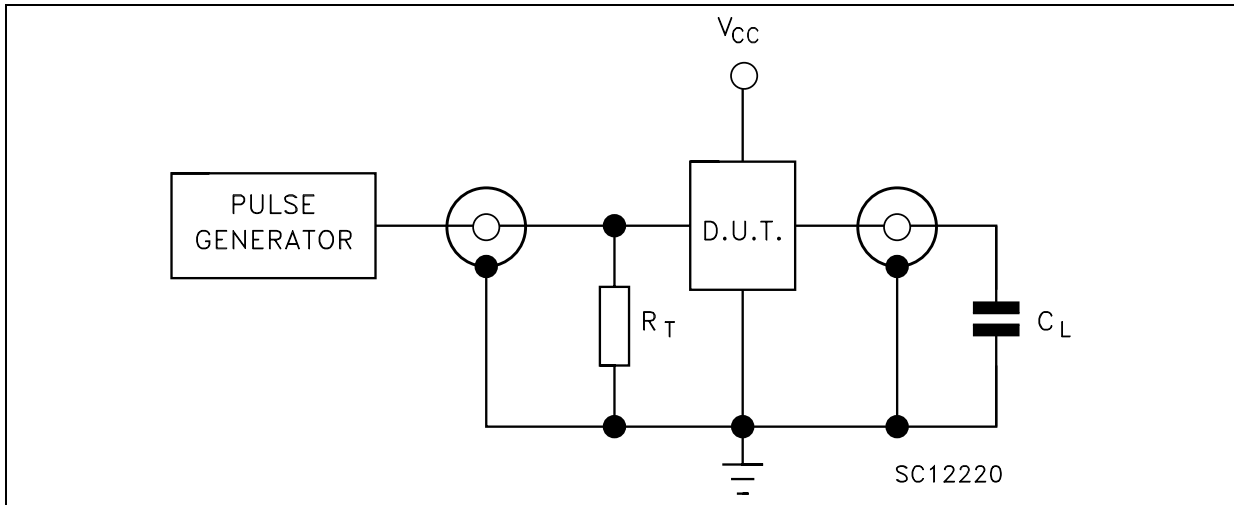
Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$t_{TLH} \ t_{THL}$	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
$t_{PLH} \ t_{PHL}$	Propagation Delay Time (D - Q)	2.0			39	100		125		150	ns
		4.5			13	20		25		30	
		6.0			11	17		21		26	
$t_{PLH} \ t_{PHL}$	Propagation Delay Time (G-Q)	2.0			39	100		125		150	ns
		4.5			13	20		25		30	
		6.0			11	17		21		26	
$t_{W(H)}$	Minimum Pulse Width (G)	2.0			15	75		95		110	ns
		4.5			6	15		19		22	
		6.0			6	13		16		19	
$t_s$	Minimum Set-up Time	2.0			15	50		65		75	ns
		4.5			3	10		13		15	
		6.0			3	9		11		13	
$t_h$	Minimum Hold Time	2.0				25		30		40	ns
		4.5				5		6		8	
		6.0				4		5		7	

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$C_{IN}$	Input Capacitance	5.0			5	10		10		10	pF
$C_{PD}$	Power Dissipation Capacitance (note 1)	5.0			20						pF

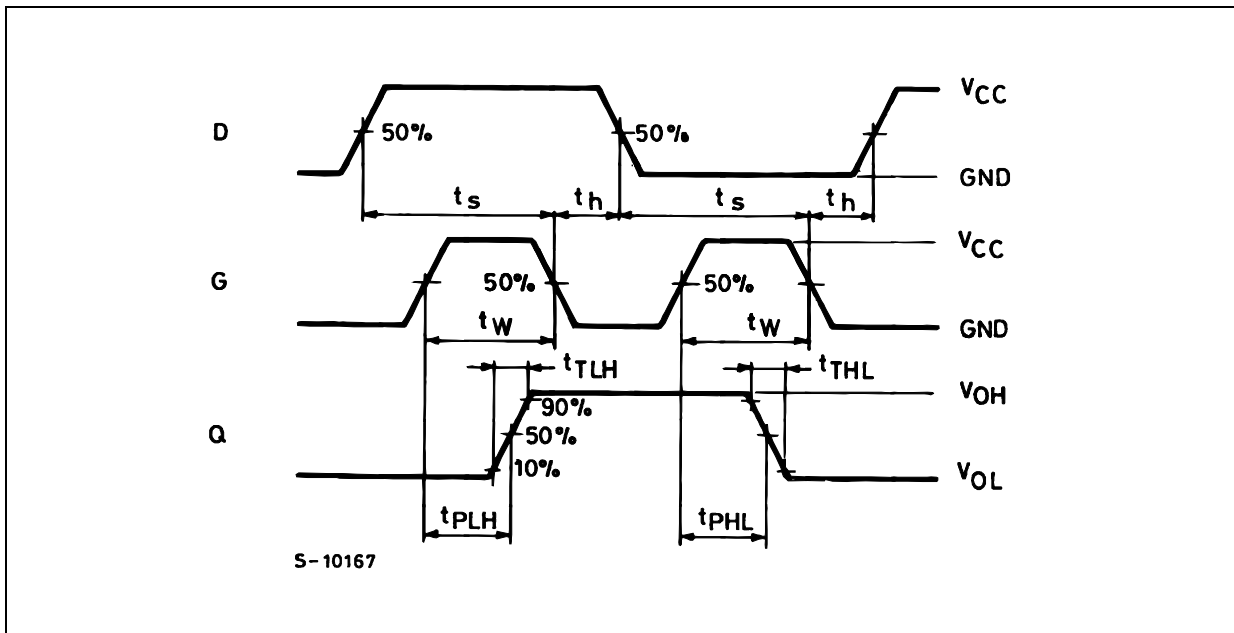
1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$  (per LATCH)

TEST CIRCUIT



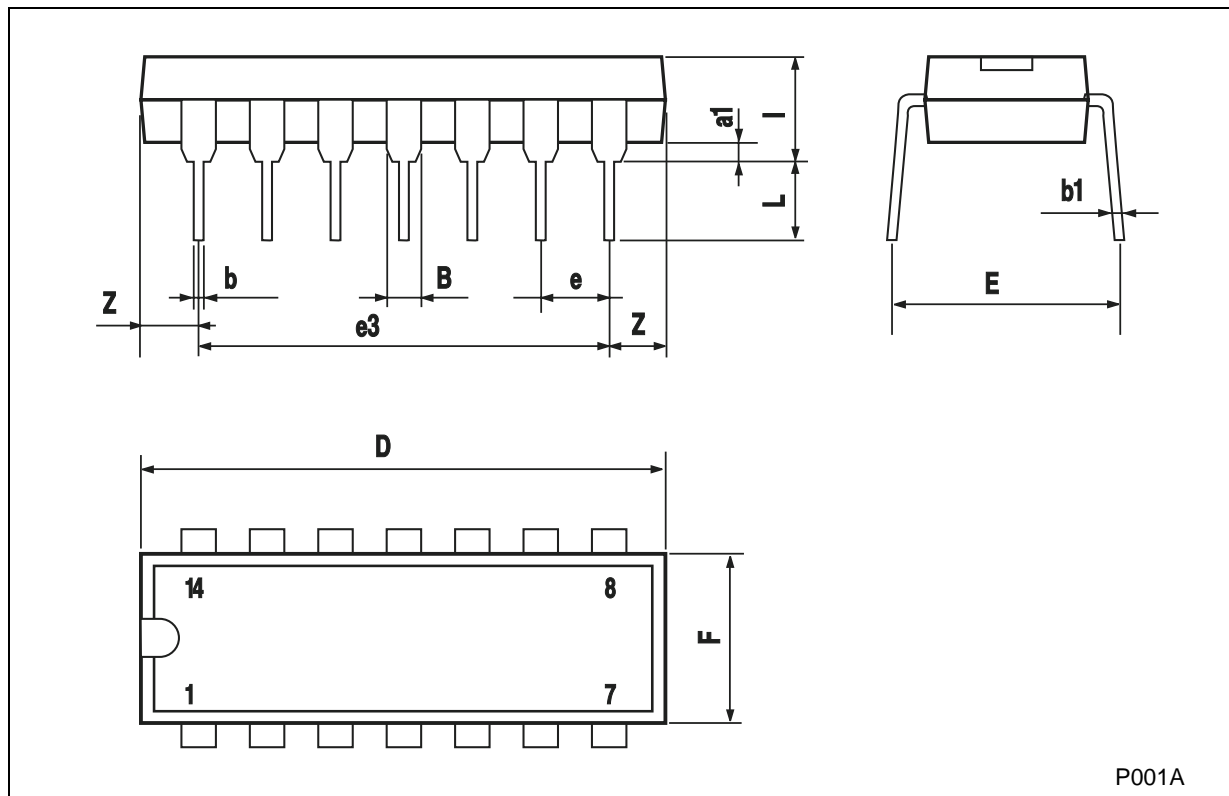
$C_L = 50\text{pF}$  or equivalent (includes jig and probe capacitance)  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

**WAVEFORM : PROPAGATION DELAY, MINIMUM PULSE WIDTH, SETUP AND HOLD TIME** ( $f=1\text{MHz}$ ; 50% duty cycle)



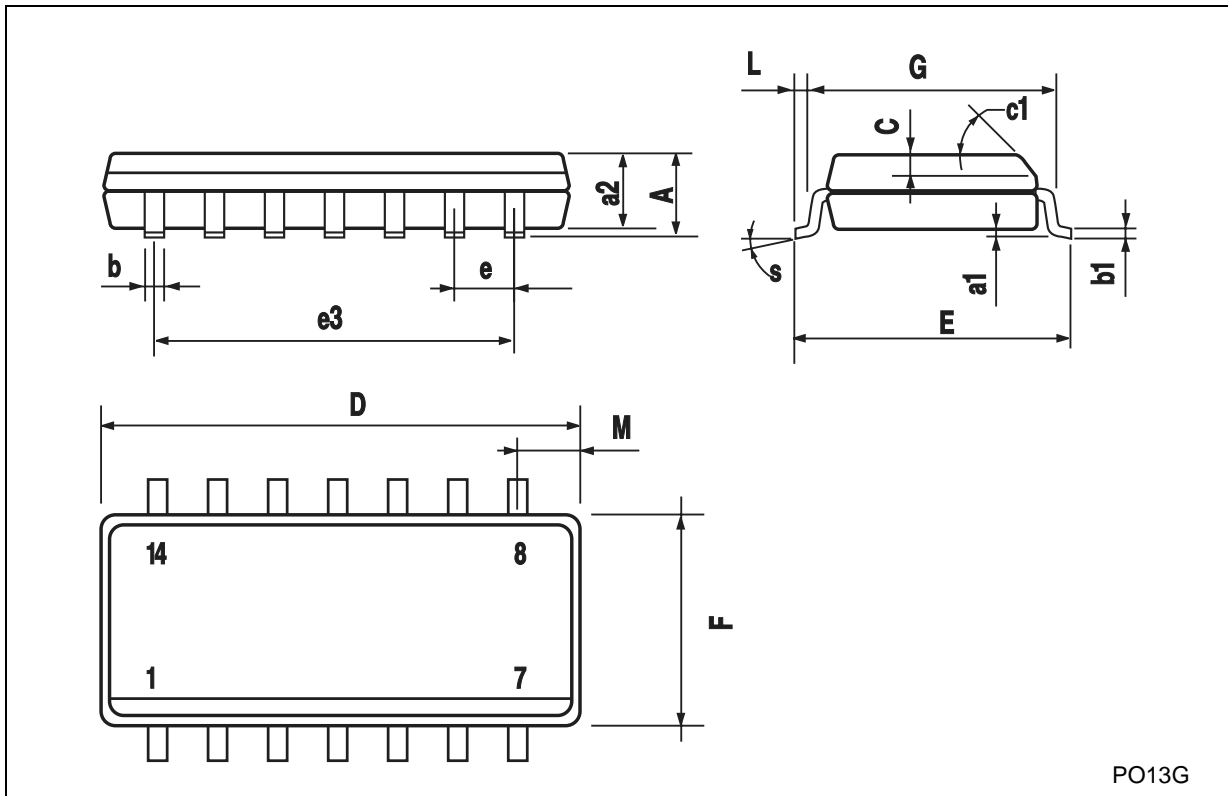
<b>Plastic DIP-14 MECHANICAL DATA</b>						
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DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



**SO-14 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					

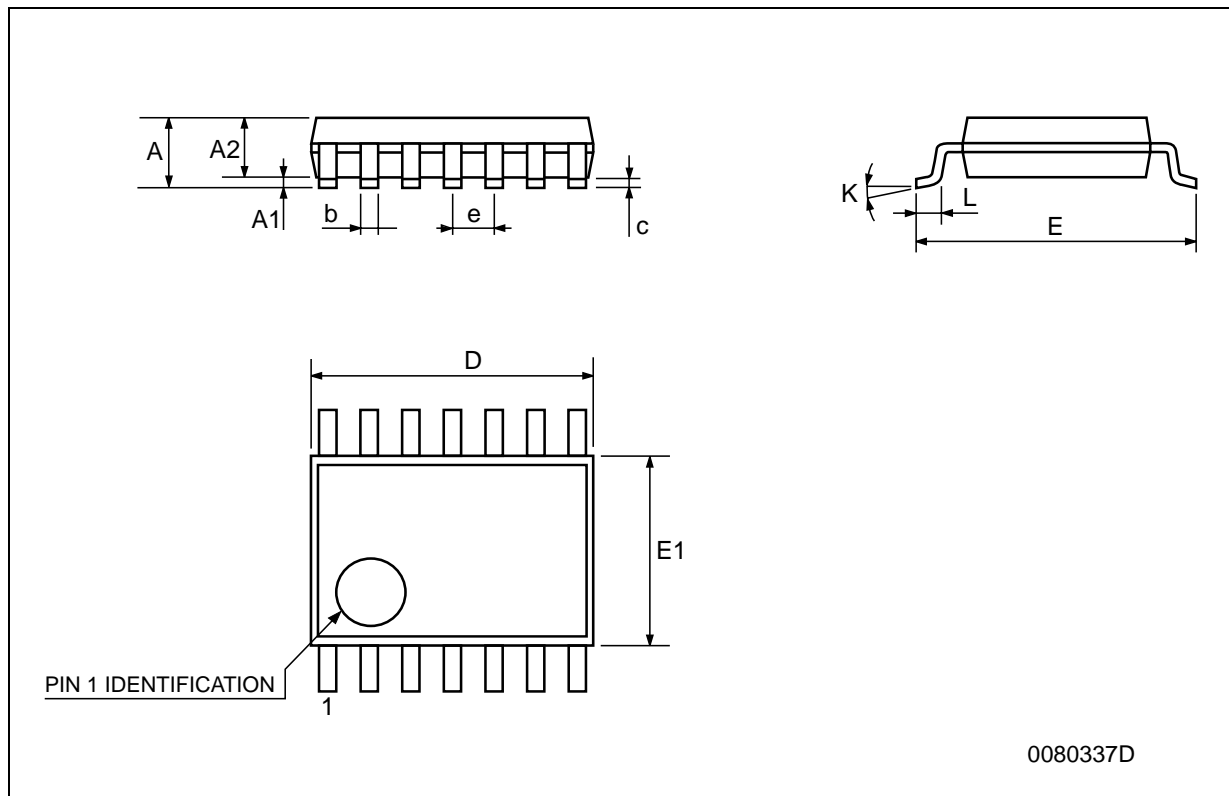


PO13G



## TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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